

Discrete POWER & Signal **Technologies**

2N3390 2N3391 2N3391A 2N3392 2N3393



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	25	V	
V _{CBO}	Collector-Base Voltage	25	V	
V _{EBO}	Emitter-Base Voltage 5.		V	
Ic	Collector Current - Continuous	500	mA	
TJ, Tsta	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		2N3390 / 3391/A / 3392 / 3393		
P_D	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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3390-93, Rev B

NPN General Purpose Amplifier (continued)

Symbol	Parameter Test Conditions		Min	Max	Units
055 014	A DA OTEDIOTION				
OFF CHA	ARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	25		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	25		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
	Collector-Cutoff Current	$V_{CB} = 18 \text{ V}, I_{E} = 0$		100	nA
I _{CBO}					

ON CHARACTERISTICS*

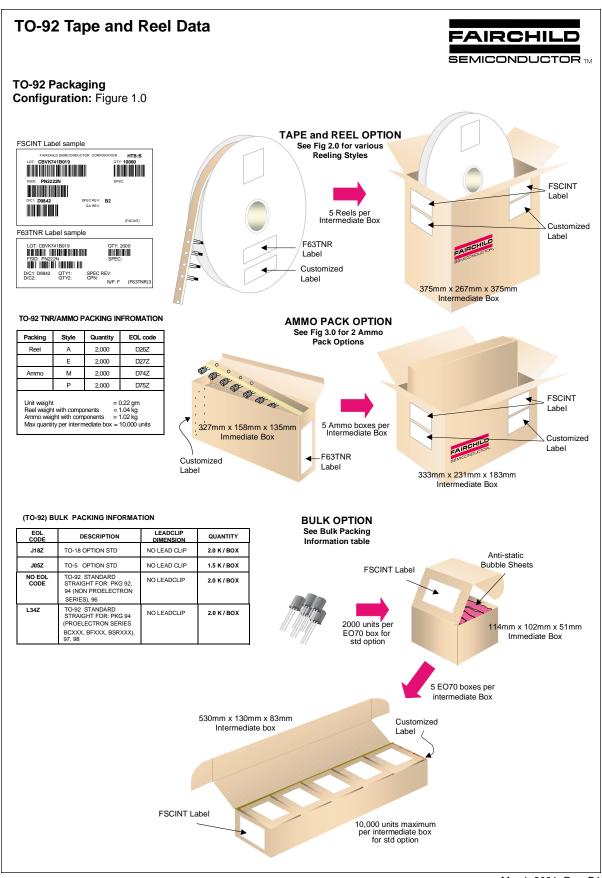
h _{FE}	DC Current Gain	$V_{CE} = 4.5 \text{ V}, I_{C} = 2.0 \text{ mA}$			
		2N3390	400	800	
		2N3391/A	250	500	
		2N3392	150	300	
		2N3393	90	180	

SMALL SIGNAL CHARACTERISTICS

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C _{ob}	Output Capacitance	V _{CB} = 10 V, f =	V _{CB} = 10 V, f = 1.0 MHz		10	pF
h _{fe}	Small-Signal Current Gain	I _C = 2.0 mA, V _C f = 1.0 kHz	E = 4.5 V, 2N3390 2N3391/A 2N3392 2N3393	400 250 150 90	1250 800 500 400	
NF	Noise Figure	$V_{CE} = 4.5 \text{ V}, I_{C} = R_{G} = 500 \Omega,$ $B_{W} = 15.7 \text{ kHz}$			5.0	dB

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

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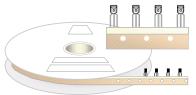
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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0

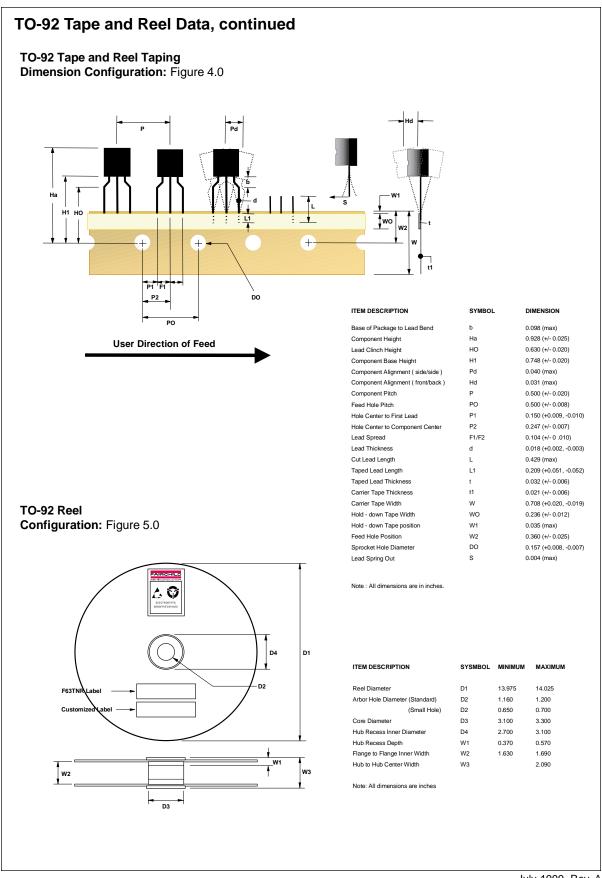


FIRST WIRE OFF IS EMITTER
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

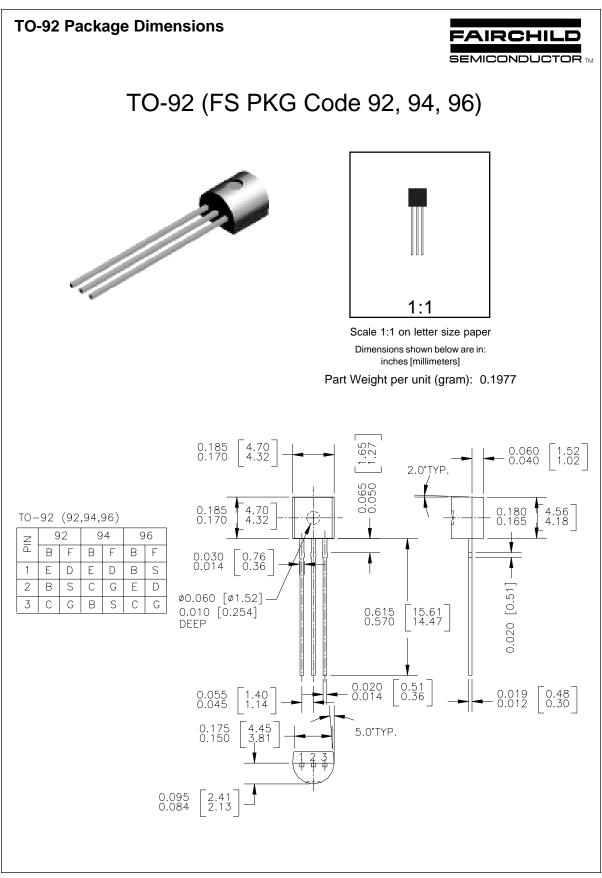
ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR (ON PKG. 92)
ADHESIVE TAPE IS ON BOTTOM SIDE
FLAT OF TRANSISTOR IS ON TOP

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Rev. G